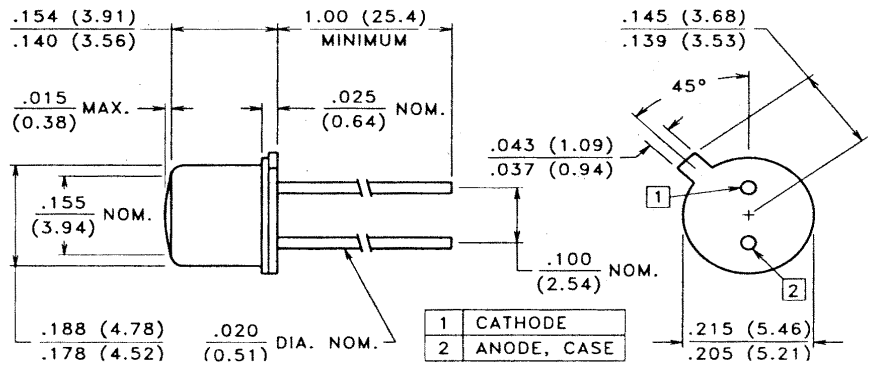
GaAlAs Infrared Emitting Diodes

TO-46 Flat Window Package — 880 nm

VTE1063

PACKAGE DIMENSIONS inch (mm)



CASE 24 TO-46 HERMETIC (Flat Window)
CHIP SIZE: .018" x .018"

DESCRIPTION

This wide beam angle TO-46 hermetic emitter contains a large area, double wirebonded, GaAlAs, 880 nm, high efficiency IRED chip suitable for higher current pulse applications.

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures	
Storage and Operating:	-55°C to 125°C
Continuous Power Dissipation:	200 mW
Derate above 30°C:	2.11 mW/°C
Maximum Continuous Current:	100 mA
Derate above 30°C:	1.05 mA/°C
Peak Forward Current, 10 µs, 100 pps:	3A
Temp. Coefficient of Power Output (Typ.):	-.8%/°C
Maximum Reverse Voltage:	5.0V
Maximum Reverse Current @ V_R = 5V:	10 µA
Peak Wavelength (Typical):	880 nm
Junction Capacitance @ 0V, 1 MHz (Typ.):	35 pF
Response Time @ I_F = 20 mA	
Rise: 1.0 µs Fall: 1.0 µs	
Lead Soldering Temperature:	260°C
(1.6 mm from case, 5 seconds max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output							Forward Drop		Half Power Beam Angle
	Irradiance				Radiant Intensity	Total Power	Test Current	V_F		
	E_e		Condition		I_e	P_O	I_{FT}	@ I_{FT}		$\theta_{1/2}$
	mW/cm^2		distance	Diameter	mW/sr	mW	mA (Pulsed)	Volts		Typ.
	Min.	Typ.	mm	mm	Min.	Typ.		Typ.	Max.	
VTE1063	3.8	5.0	36	6.4	49	80	1.0	2.8	3.5	±35°

■ Refer to General Product Notes, page 2.